

SEMiX402GAL066HDs



SEMiX[®] 2s

Trench IGBT Modules

SEMiX402GAL066HDs

Features

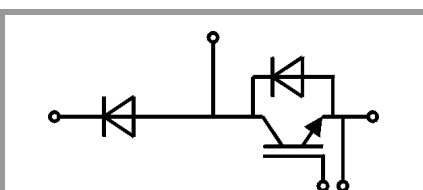
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- Matrix Converter
- Resonant Inverter
- Current Source Inverter

Remarks

- Case temperature limited to $T_C=125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j=150^\circ\text{C}$
- For short circuit: Soft R_{Goff} recommended
- Take care of over-voltage caused by stray inductance



GAL

| Absolute Maximum Ratings | | | | |
|---------------------------|--|---------------------------|-------------|------------------|
| Symbol | Conditions | | Values | Unit |
| IGBT | | | | |
| V_{CES} | $T_j = 25^\circ\text{C}$ | | 600 | V |
| I_C | $T_j = 175^\circ\text{C}$ | $T_c = 25^\circ\text{C}$ | 502 | A |
| | | $T_c = 80^\circ\text{C}$ | 379 | A |
| I_{Cnom} | | | 400 | A |
| I_{CRM} | $I_{CRM} = 2 \times I_{Cnom}$ | | 800 | A |
| V_{GES} | | | -20 ... 20 | V |
| t_{psc} | $V_{CC} = 360\text{ V}$ | $T_j = 150^\circ\text{C}$ | 6 | μs |
| | $V_{GE} \leq 15\text{ V}$ | | | |
| | $V_{CES} \leq 600\text{ V}$ | | | |
| T_j | | | -40 ... 175 | $^\circ\text{C}$ |
| Inverse diode | | | | |
| I_F | $T_j = 175^\circ\text{C}$ | $T_c = 25^\circ\text{C}$ | 543 | A |
| | | $T_c = 80^\circ\text{C}$ | 397 | A |
| I_{Fnom} | | | 400 | A |
| I_{FRM} | $I_{FRM} = 2 \times I_{Fnom}$ | | 800 | A |
| I_{FSM} | $t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$ | | 1800 | A |
| T_j | | | -40 ... 175 | $^\circ\text{C}$ |
| Freewheeling diode | | | | |
| I_F | $T_j = 175^\circ\text{C}$ | $T_c = 25^\circ\text{C}$ | 566 | A |
| | | $T_c = 80^\circ\text{C}$ | 412 | A |
| I_{Fnom} | | | 400 | A |
| I_{FRM} | $I_{FRM} = 2 \times I_{Fnom}$ | | 800 | A |
| I_{FSM} | $t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$ | | 1800 | A |
| T_j | | | -40 ... 175 | $^\circ\text{C}$ |
| Module | | | | |
| $I_{t(RMS)}$ | $T_{terminal} = 80^\circ\text{C}$ | | 600 | A |
| T_{stg} | | | -40 ... 125 | $^\circ\text{C}$ |
| V_{isol} | AC sinus 50Hz, $t = 1\text{ min}$ | | 4000 | V |

| Characteristics | | | | | | |
|-----------------|--|---------------------------|------|------|------|------------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| IGBT | | | | | | |
| $V_{CE(sat)}$ | $I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel | $T_j = 25^\circ\text{C}$ | 1.45 | 1.85 | | V |
| | | $T_j = 150^\circ\text{C}$ | 1.7 | 2.1 | | V |
| V_{CE0} | | $T_j = 25^\circ\text{C}$ | 0.9 | 1 | | V |
| | | $T_j = 150^\circ\text{C}$ | 0.85 | 0.9 | | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ | $T_j = 25^\circ\text{C}$ | 1.4 | 2.1 | | $\text{m}\Omega$ |
| | | $T_j = 150^\circ\text{C}$ | 2.1 | 3.0 | | $\text{m}\Omega$ |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}, I_C = 6.4\text{ mA}$ | | 5 | 5.8 | 6.5 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$ $V_{CE} = 600\text{ V}$ | $T_j = 25^\circ\text{C}$ | 0.15 | 0.45 | | mA |
| | | $T_j = 150^\circ\text{C}$ | | | | mA |
| C_{ies} | $V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$ | $f = 1\text{ MHz}$ | | 24.7 | | nF |
| C_{oes} | | $f = 1\text{ MHz}$ | | 1.54 | | nF |
| C_{res} | | $f = 1\text{ MHz}$ | | 0.73 | | nF |
| Q_G | $V_{GE} = -8\text{ V...} + 15\text{ V}$ | | | 3200 | | nC |
| R_{Gint} | $T_j = 25^\circ\text{C}$ | | | 1.00 | | Ω |

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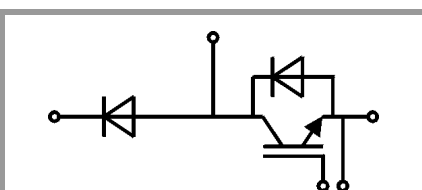
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- For short circuit: Soft R_{Goff} recommended
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| Characteristics | | | | | | |
|--------------------|--|---------------------------|------|---------------|------|---------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| $t_{d(on)}$ | $V_{CC} = 300\text{ V}$ | $T_j = 150^\circ\text{C}$ | | 150 | | ns |
| t_r | $I_C = 400\text{ A}$ | $T_j = 150^\circ\text{C}$ | | 125 | | ns |
| E_{on} | $V_{GE} = \pm 15\text{ V}$ | $T_j = 150^\circ\text{C}$ | | 22 | | mJ |
| $t_{d(off)}$ | $R_{G\ on} = 4.5\ \Omega$ | $T_j = 150^\circ\text{C}$ | | 900 | | ns |
| t_f | $R_{G\ off} = 4.5\ \Omega$ | $T_j = 150^\circ\text{C}$ | | 65 | | ns |
| E_{off} | | $T_j = 150^\circ\text{C}$ | | 24 | | mJ |
| $R_{th(j-c)}$ | per IGBT | | | | 0.12 | K/W |
| Inverse diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 400\text{ A}$ | $T_j = 25^\circ\text{C}$ | | 1.4 | 1.60 | V |
| | $V_{GE} = 0\text{ V}$ chip | $T_j = 150^\circ\text{C}$ | | 1.4 | 1.6 | V |
| V_{F0} | | $T_j = 25^\circ\text{C}$ | 0.9 | 1 | 1.1 | V |
| | | $T_j = 150^\circ\text{C}$ | 0.75 | 0.85 | 0.95 | V |
| r_F | | $T_j = 25^\circ\text{C}$ | 0.8 | 1.0 | 1.3 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | 1.1 | 1.4 | 1.6 | m Ω |
| I_{RRM} | $I_F = 400\text{ A}$ | $T_j = 150^\circ\text{C}$ | | 250 | | A |
| Q_{rr} | $di/dt_{off} = 3700\text{ A}/\mu\text{s}$ | $T_j = 150^\circ\text{C}$ | | 47 | | μC |
| E_{rr} | $V_{GE} = -8\text{ V}$ | $T_j = 150^\circ\text{C}$ | | 10 | | mJ |
| | $V_{CC} = 300\text{ V}$ | $T_j = 150^\circ\text{C}$ | | | | |
| $R_{th(j-c)}$ | per diode | | | | 0.15 | K/W |
| Freewheeling diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 400\text{ A}$ | $T_j = 25^\circ\text{C}$ | | 1.3 | 1.53 | V |
| | $V_{GE} = 0\text{ V}$ chip | $T_j = 150^\circ\text{C}$ | | 1.3 | 1.5 | V |
| V_{F0} | | $T_j = 25^\circ\text{C}$ | 0.9 | 1 | 1.1 | V |
| | | $T_j = 150^\circ\text{C}$ | 0.75 | 0.85 | 0.95 | V |
| r_F | | $T_j = 25^\circ\text{C}$ | 0.7 | 0.9 | 1.1 | m Ω |
| | | $T_j = 150^\circ\text{C}$ | 1.0 | 1.2 | 1.4 | m Ω |
| I_{RRM} | $I_F = 400\text{ A}$ | $T_j = 150^\circ\text{C}$ | | 250 | | A |
| Q_{rr} | $di/dt_{off} = 3700\text{ A}/\mu\text{s}$ | $T_j = 150^\circ\text{C}$ | | 47 | | μC |
| E_{rr} | $V_{GE} = -8\text{ V}$ | $T_j = 150^\circ\text{C}$ | | 10 | | mJ |
| | $V_{CC} = 300\text{ V}$ | $T_j = 150^\circ\text{C}$ | | | | |
| $R_{th(j-c)}$ | per diode | | | | 0.15 | K/W |
| Module | | | | | | |
| L_{CE} | | | | 18 | | nH |
| R_{CC+EE} | res., terminal-chip | $T_C = 25^\circ\text{C}$ | | 0.7 | | m Ω |
| | | $T_C = 125^\circ\text{C}$ | | 1 | | m Ω |
| $R_{th(c-s)}$ | per module | | | 0.045 | | K/W |
| M_s | to heat sink (M5) | | 3 | | 5 | Nm |
| M_t | | to terminals (M6) | 2.5 | | 5 | Nm |
| | | | | | | Nm |
| w | | | | | 250 | g |
| Temperatur Sensor | | | | | | |
| R_{100} | $T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$) | | | 493 \pm 5% | | Ω |
| $B_{100/125}$ | $R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; T[K]; | | | 3550 \pm 2% | | K |



GAL

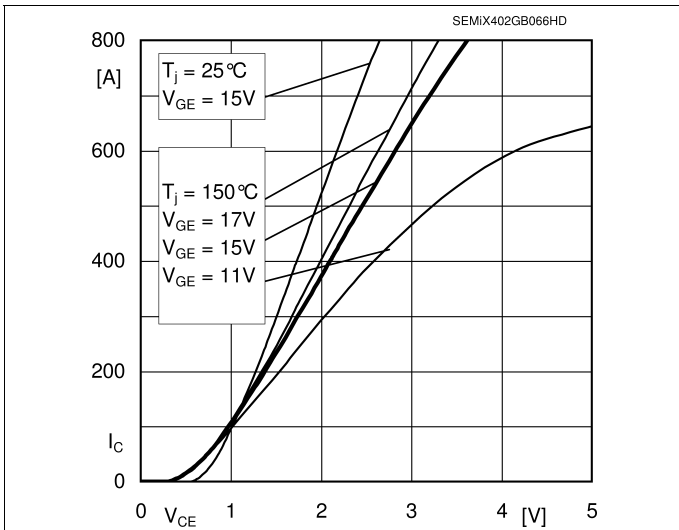


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

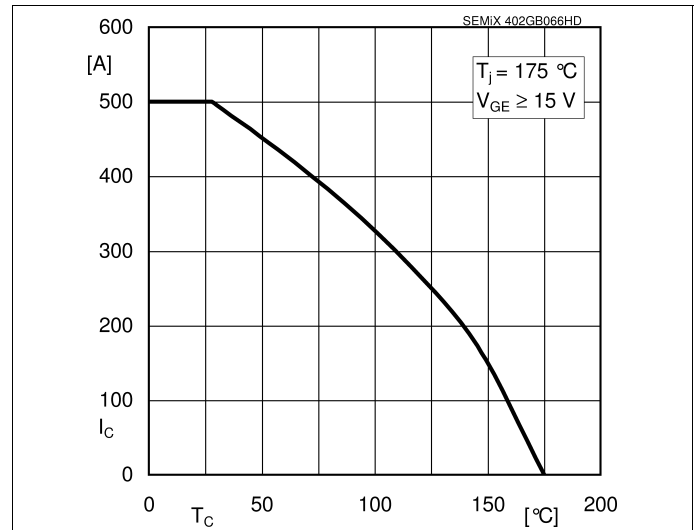


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

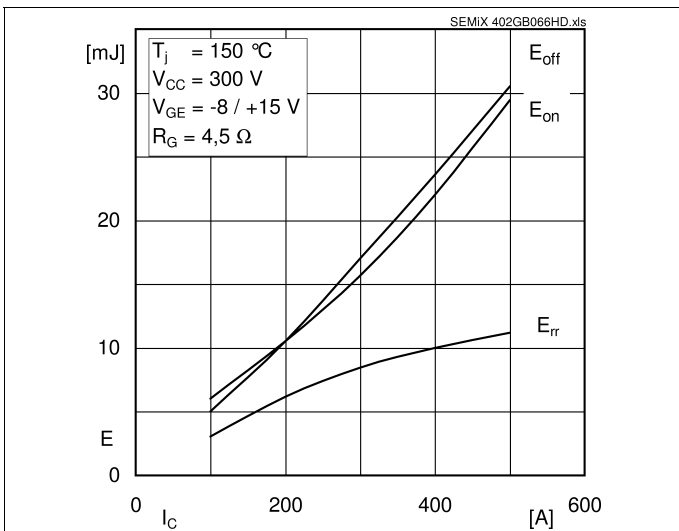


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

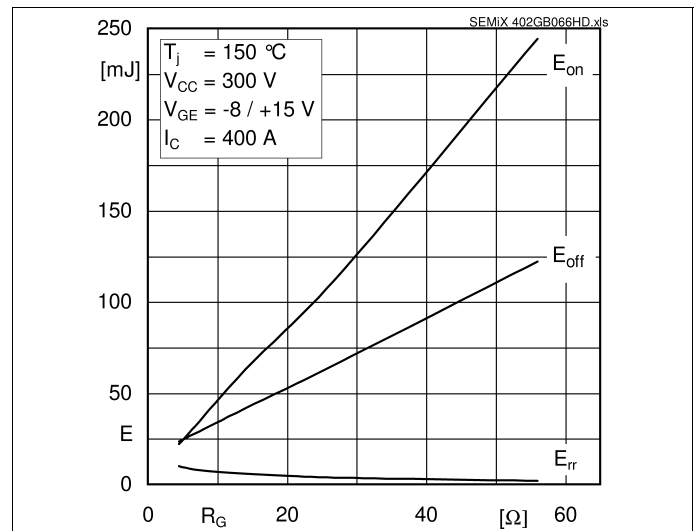


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

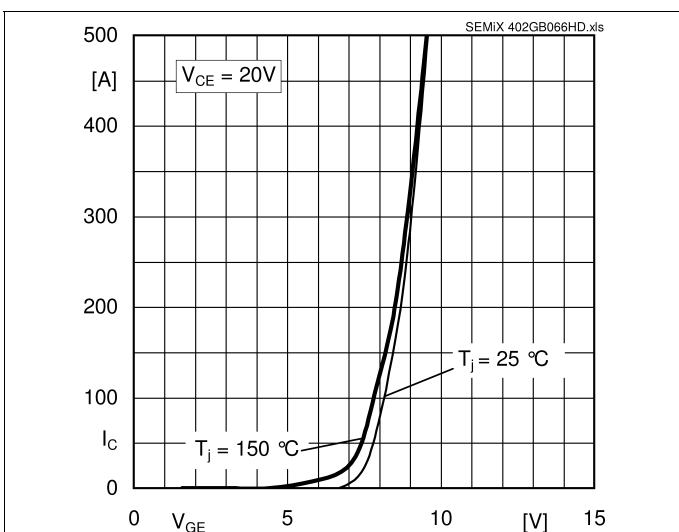


Fig. 5: Typ. transfer characteristic

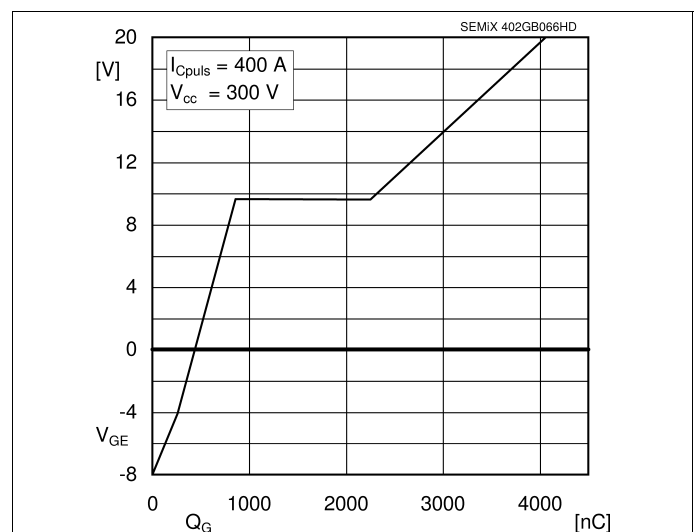


Fig. 6: Typ. gate charge characteristic

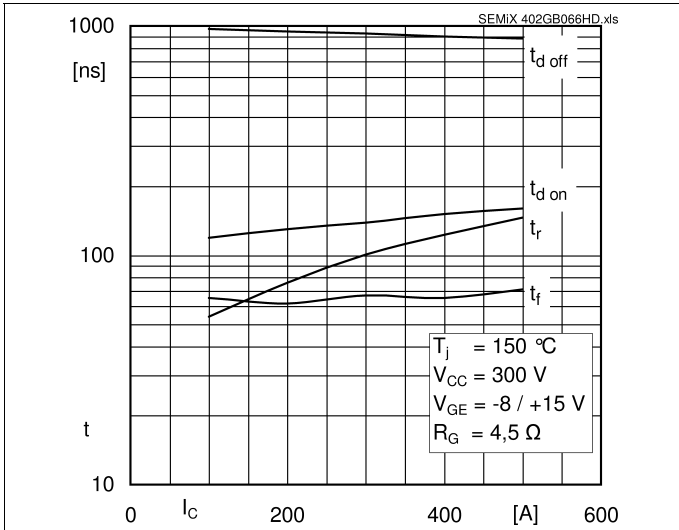


Fig. 7: Typ. switching times vs. I_C

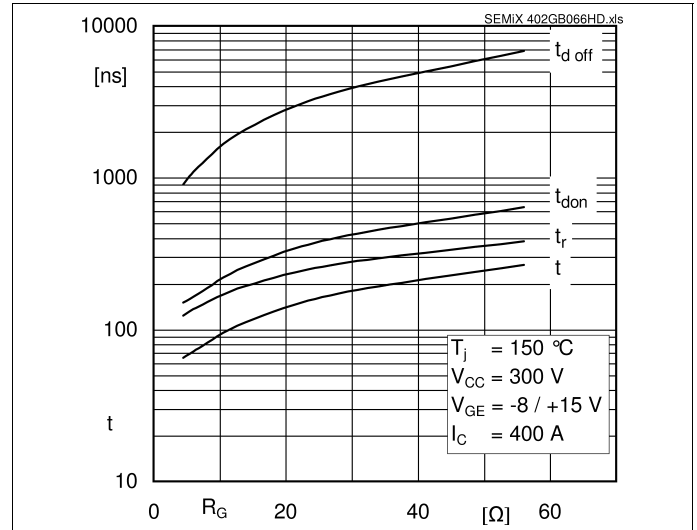


Fig. 8: Typ. switching times vs. gate resistor R_G

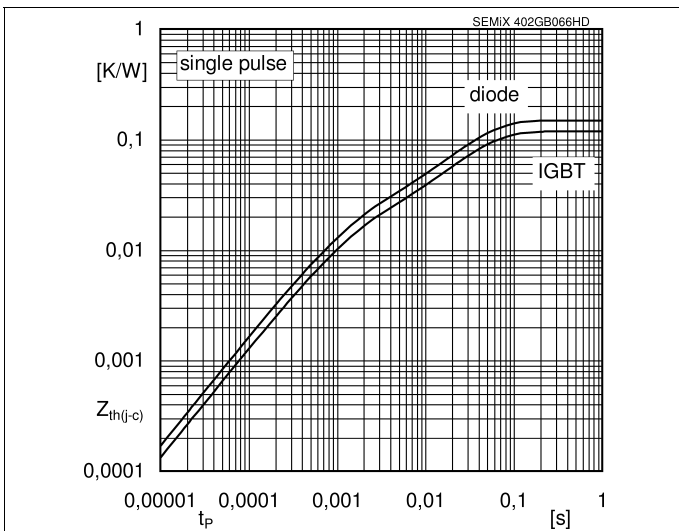


Fig. 9: Typ. transient thermal impedance

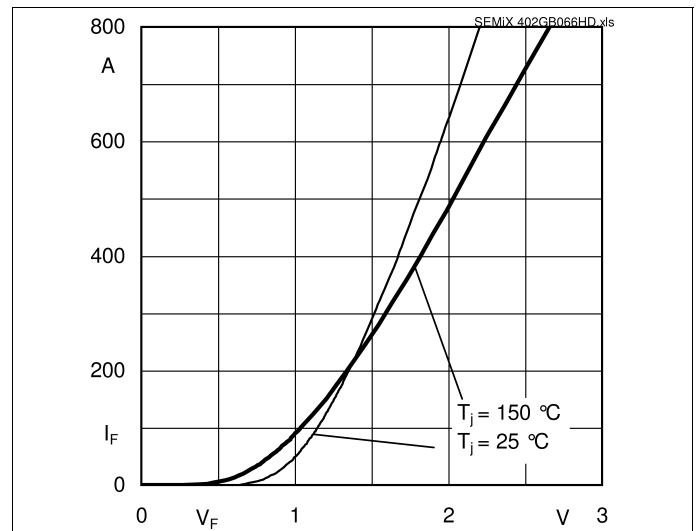


Fig. 10: Typ. CAL diode forward charact., incl. R_{CC+EE}

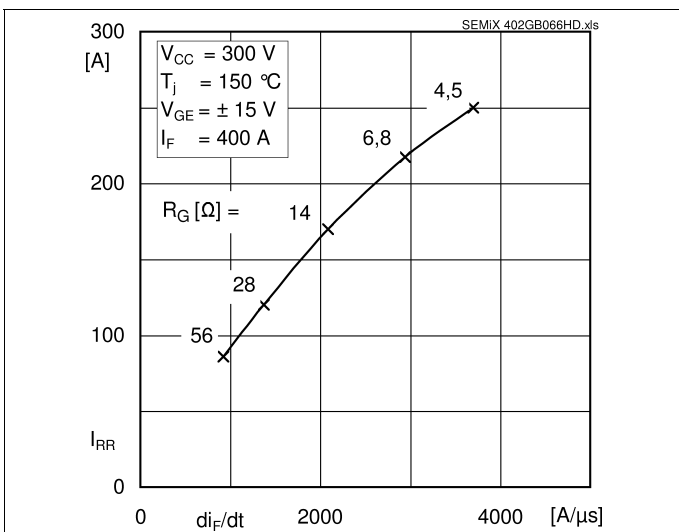


Fig. 11: Typ. CAL diode peak reverse recovery current

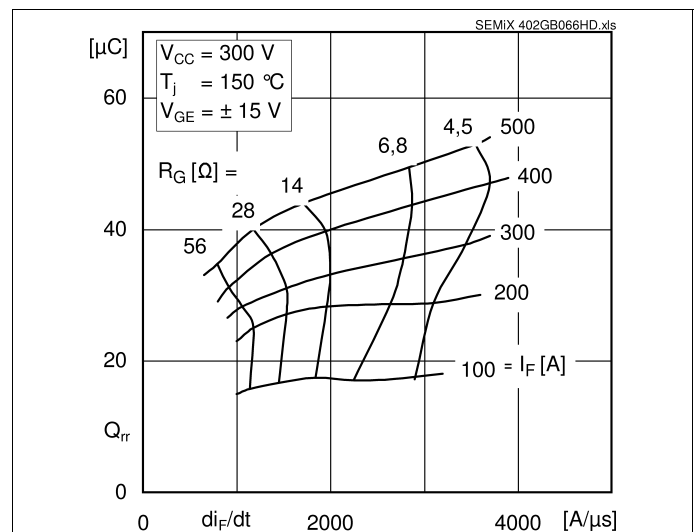
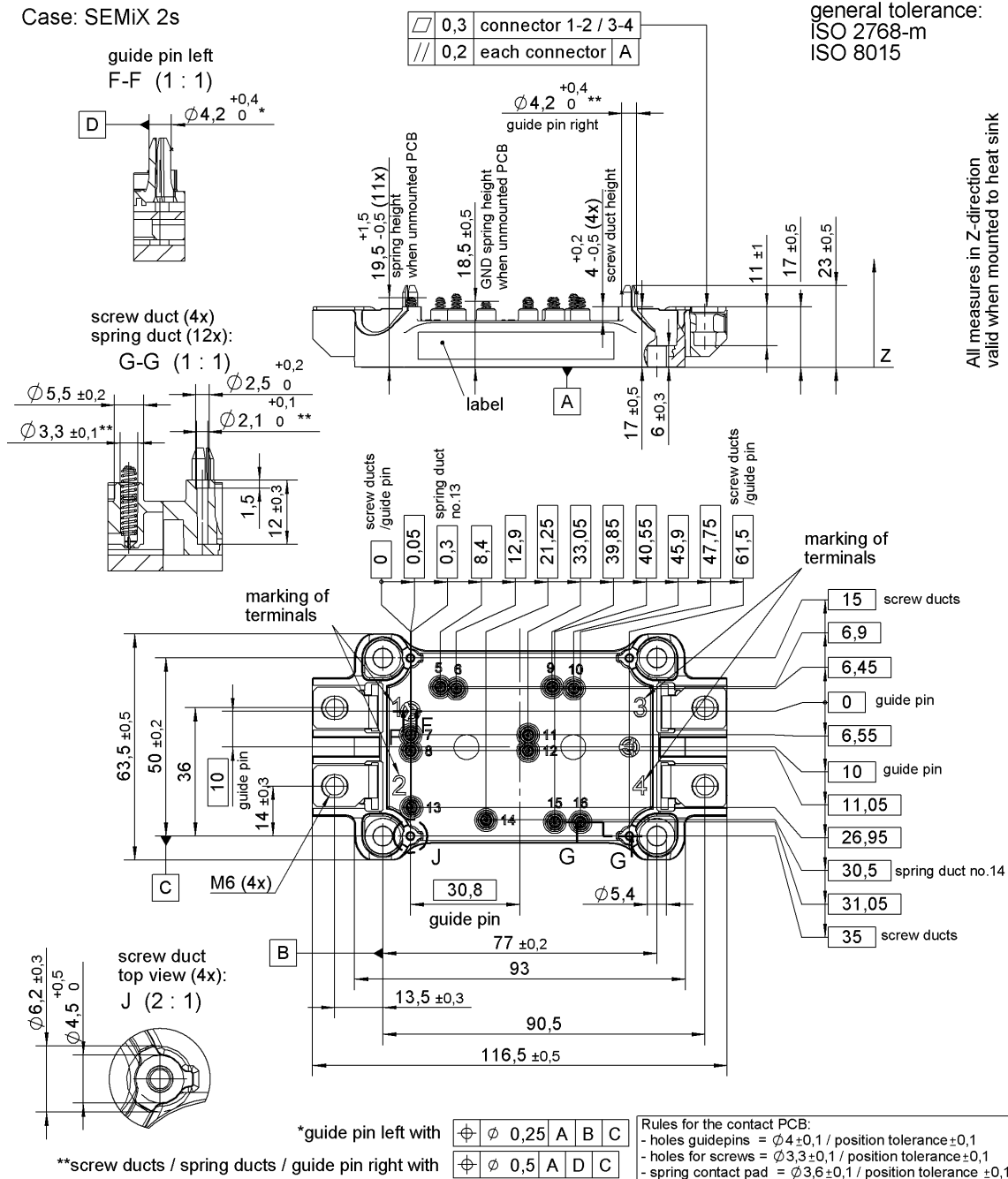


Fig. 12: Typ. CAL diode recovery charge

SEMiX402GAL066HDs

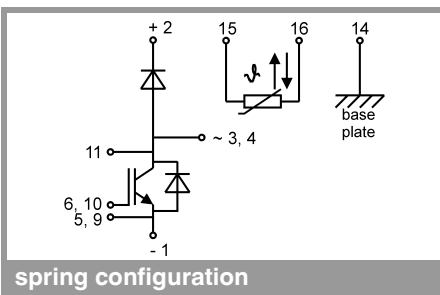
Case: SEMiX 2s

general tolerance:
ISO 2768-m
ISO 8015



All measures in Z-direction
valid when mounted to heat sink

SEMIX 2s



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.